DRA4144E

Silicon PNP epitaxial planar type

For digital circuits Complementary to DRC4144E DRA2144E in NS through hole type package

Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Contributes to miniaturization of sets, mount area reduction
- Eco-friendly Halogen-free package

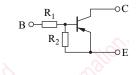
Packaging

DRA4144E0A Radial type: 5000 pcs / carton

Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	-50	V
Collector-emitter voltage (Base open)	V _{CEO}	-50	V
Collector current	I _C	-100	mA
Total power dissipation	P _T	300	mW
Junction temperature	Tj	150	°C
Storage temperature	T _{stg}	-55 to +150	O°C S

- Package
- Code
- NS-B2-B-B
 - Package dimension clicks here. \rightarrow
- Pin Name
- 1: Emitter
- 2: Collector
- 3: Base
- Marking Symbol: LL
- Internal Connection



Resistance value	R ₁	47	kΩ
	R ₂	47	kΩ
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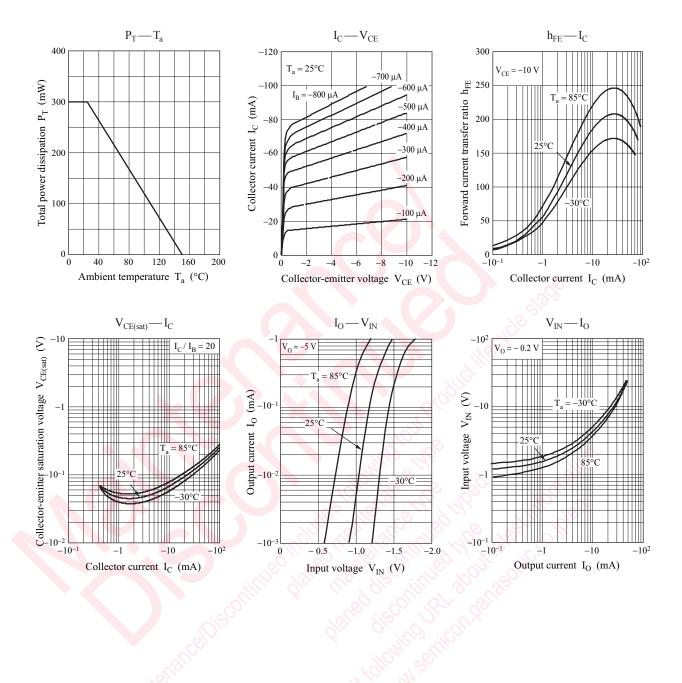
Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min) Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \ \mu A, I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{\rm CB} = -50$ V, $I_{\rm E} = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = -50 \text{ V}, I_B = 0$			- 0.5	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{\rm EB} = -6$ V, $I_{\rm C} = 0$			- 0.1	mA
Forward current transfer ratio	\mathbf{h}_{FE}	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	80			
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -10$ mA, $I_{\rm B} = -0.5$ mA			-0.25	V
Input voltage (ON)	V _{I(on)}	$V_{\rm CE} = -0.2$ V, $I_{\rm C} = -5$ mA	-3.6			V
Input voltage (OFF)	V _{I(off)}	$V_{CE} = -5 \text{ V}, I_C = -100 \mu\text{A}$			- 0.8	V
Input resistance	R ₁		-30%	47	+30%	kΩ
Resistance ratio	R_1/R_2		0.8	1.0	1.2	

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

DRA4144E

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